

A new thermal low temperature ALD process for Nickel utilizing Dichlorobis(triethylphosphine)nickel(II) and 1,4-bis(trimethylgermyl)-1,4- dihydropyrazine

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Figure S1: TG curves for different cobalt precursors

Figure S2: Film uniformity as a function of distance from the inlet area

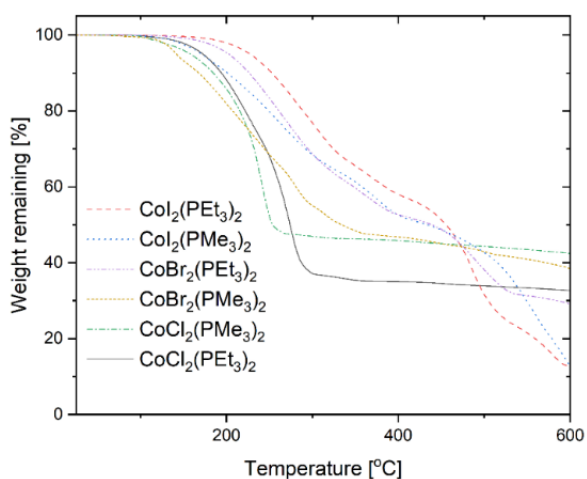


Figure S1. TG curves measured for different $\text{CoX}_2(\text{PR}_3)_2$ ($\text{X} = \text{Cl}, \text{Br}, \text{I}$; $\text{R} = \text{Me}, \text{Et}$) compounds.

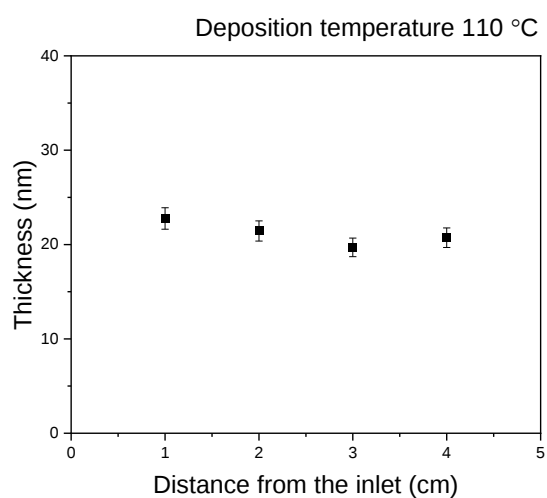


Figure S2. Film thickness across the substrate as a function of distance from the precursor inlet area.